

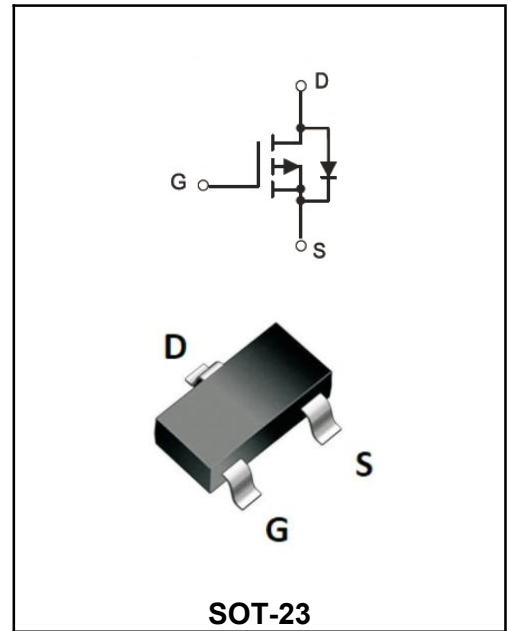
-20V P-CHANNEL ENHANCEMENT MODE MOSFET

MAIN CHARACTERISTICS

| | |
|--|-----------------------------|
| I_D | -3.3A |
| V_{DSS} | -20V |
| R_{DS(on)-typ}(@V_{GS}=-4.5V) | < 80mΩ(Type:55 mΩ) |

Application

- ◆ Battery protection
- ◆ Load switch
- ◆ Uninterruptible power supply



Marking Code

YFW2301A

A1SHB

Maximum Ratings at Tc=25°C unless otherwise specified

| Characteristics | Symbols | Value | Units |
|--|------------------------|-------------|-------------|
| Drain-Source Voltage | V_{DS} | -20 | V |
| Gate - Source Voltage | V_{GS} | ± 12 | V |
| Continuous Drain Current, V _{GS} @ -4.5V ¹ @T _A =25°C | I_D | -3.3 | A |
| Continuous Drain Current, V _{GS} @ -4.5V ¹ @T _A =70°C | I_D | -2.6 | A |
| Pulsed Drain Current ² | I_{DM} | -13 | A |
| Total Power Dissipation ³ @T _A =25°C | P_D | 1.4 | W |
| Storage Temperature Range | T_{STG} | -55 to +150 | °C |
| Operating Junction Temperature Range | T_J | -55 to +150 | °C |
| Thermal Resistance Junction-Ambient ¹ | R_{θJA} | 125 | °C/W |
| Thermal Resistance Junction-ambient ¹ (t≤10s) | R_{θJA} | 90 | °C/W |

Maximum Ratings at Tc=25°C unless otherwise specified

| Characteristics | Test Condition | Symbols | Min | Typ | Max | Units |
|--|---|--------------|------|------|------|-------|
| Drain-Source Breakdown Voltage | $V_{GS}=0V, I_D=-250\mu A$ | BV_{DSS} | -20 | -22 | - | V |
| Static Drain-Source on-Resistance ² | $V_{GS}=-4.5V, I_D=-3A$ | $R_{DS(ON)}$ | - | 55 | 80 | mΩ |
| | $V_{GS}=-2.5V, I_D=-2A$ | | - | 75 | 100 | |
| Gate Threshold Voltage | $V_{DS}=V_{GS}, I_D=-250\mu A$ | $V_{GS(th)}$ | -0.5 | -0.7 | -1.2 | V |
| Drain-Source Leakage Current | $V_{DS}=-20V, V_{GS}=0V, T_J=25^\circ C$ | I_{DSS} | - | - | 1 | μA |
| | $V_{DS}=-20V, V_{GS}=0V, T_J=55^\circ C$ | | - | - | -5 | |
| Gate-Source Leakage Current | $V_{GS}=\pm 12V, V_{DS}=0V$ | I_{GSS} | - | - | ±100 | nA |
| Forward Transconductance | $V_{DS}=-5V, I_D=-3A$ | g_{fs} | - | 12.2 | - | S |
| Total Gate Charge(-4.5V) | $V_{DS}=-15V$ $V_{GS}=-4.5V$ $I_D=-3A$ | Q_g | - | 10.1 | - | nC |
| Gate-Source Charge | | Q_{gs} | - | 1.21 | - | |
| Gate-Drain Charge | | Q_{gd} | - | 2.46 | - | |
| Turn-on delay time | $V_{DD}=-10V$ $V_{GS}=-4.5V$ $I_D=-3A$ $R_{GEN}=3.3\Omega$ | $t_{d(on)}$ | - | 5.6 | - | ns |
| Rise Time | | T_r | - | 32.2 | - | |
| Turn-Off Delay Time | | $t_{d(OFF)}$ | - | 45.6 | - | |
| Fall Time | | t_f | - | 29.2 | - | |
| Input Capacitance | $V_{DS}=-15V$ $V_{GS}=0V$ $f=1MHz$ | C_{iss} | - | 677 | - | pF |
| Output Capacitance | | C_{oss} | - | 82 | - | |
| Reverse Transfer Capacitance | | C_{rss} | - | 73 | - | |
| Continuous Source Current ^{1,4} | $V_G=V_D=0V$, Force Current | I_S | - | - | -3 | A |
| Diode Forward Voltage ² | $I_F=-1A, V_{GS}=0V, T_J=25^\circ C$ | V_{SD} | - | - | -1 | V |

Note :

- 1、 The data tested by surface mounted on a 1 inch2 FR-4 board with 2OZ copper.
- 2、 The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- 3、 The power dissipation is limited by 150°C junction temperature
- 4、 The data is theoretically the same as ID and IDM , in real applications , should be limited by total power dissipation.

Ratings and Characteristic Curves

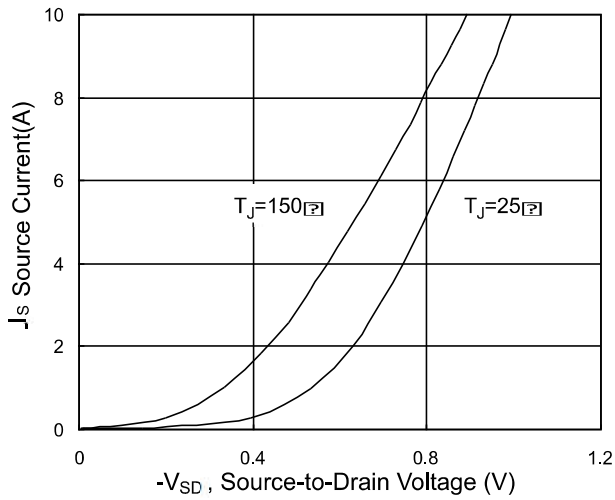


Fig.1 Typical Output Characteristics

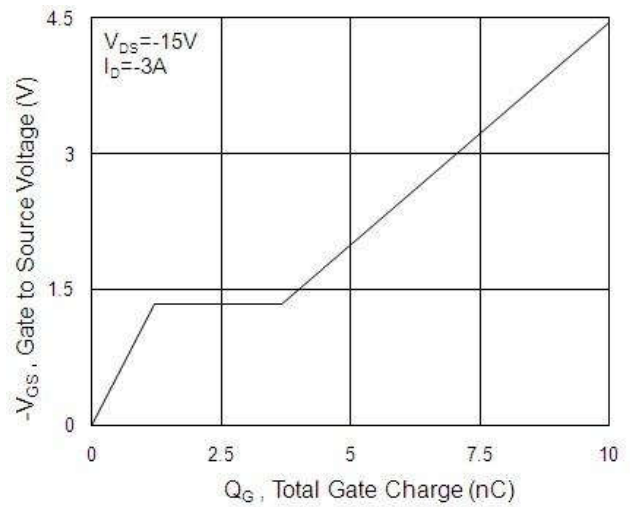
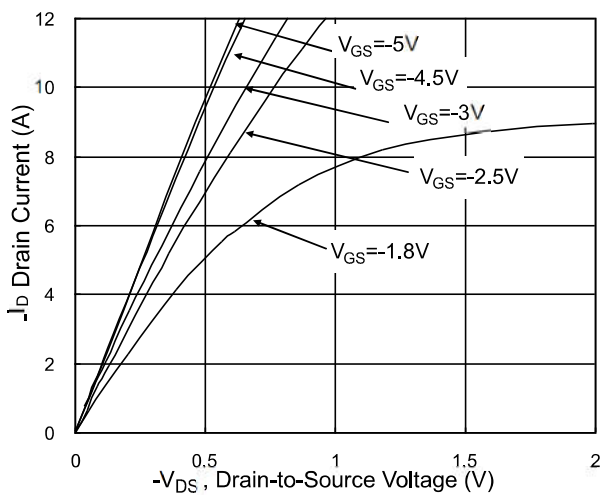


Fig.2 On-Resistance vs. G-S Voltage



Source Drain Forward Characteristics

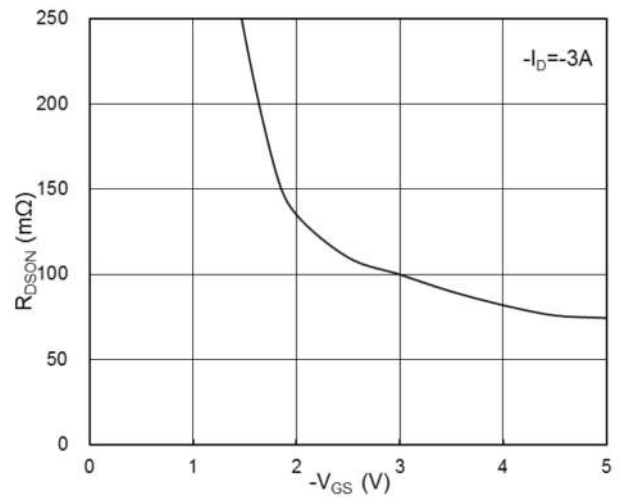
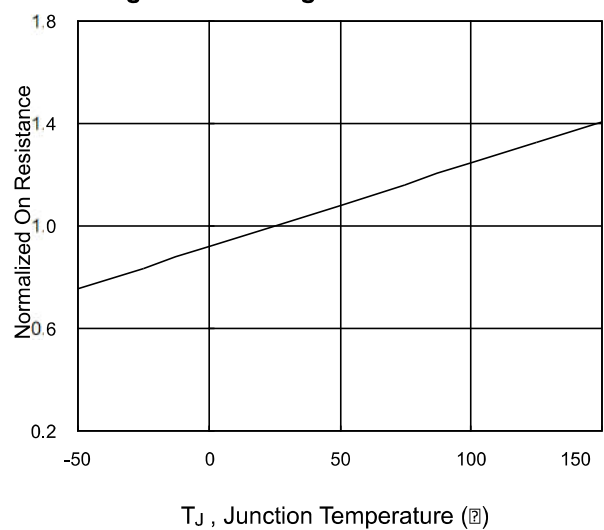
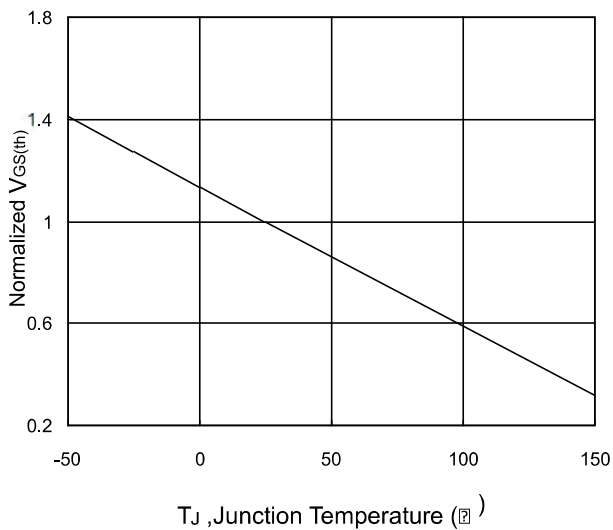


Fig.4 Gate-Charge Characteristics



Ratings and Characteristic Curves

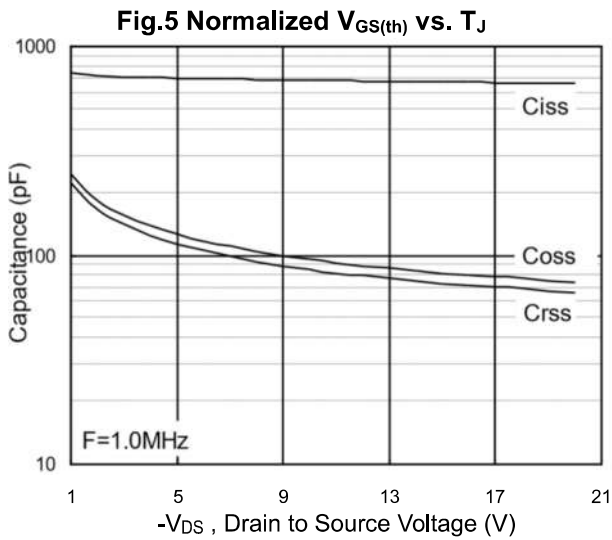


Fig.7 Capacitance

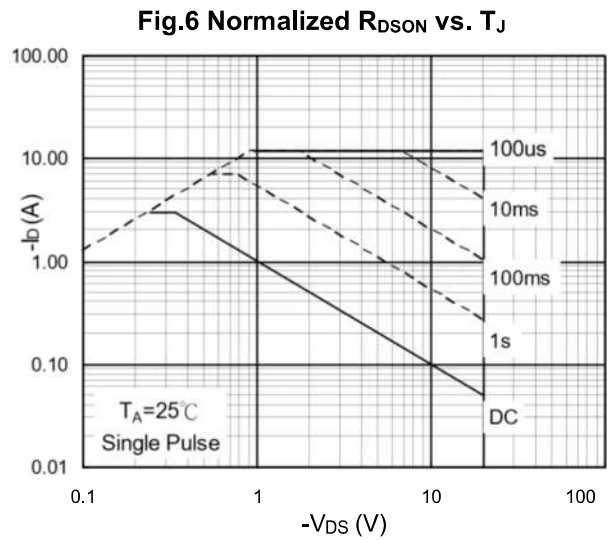


Fig.8 Safe Operating Area

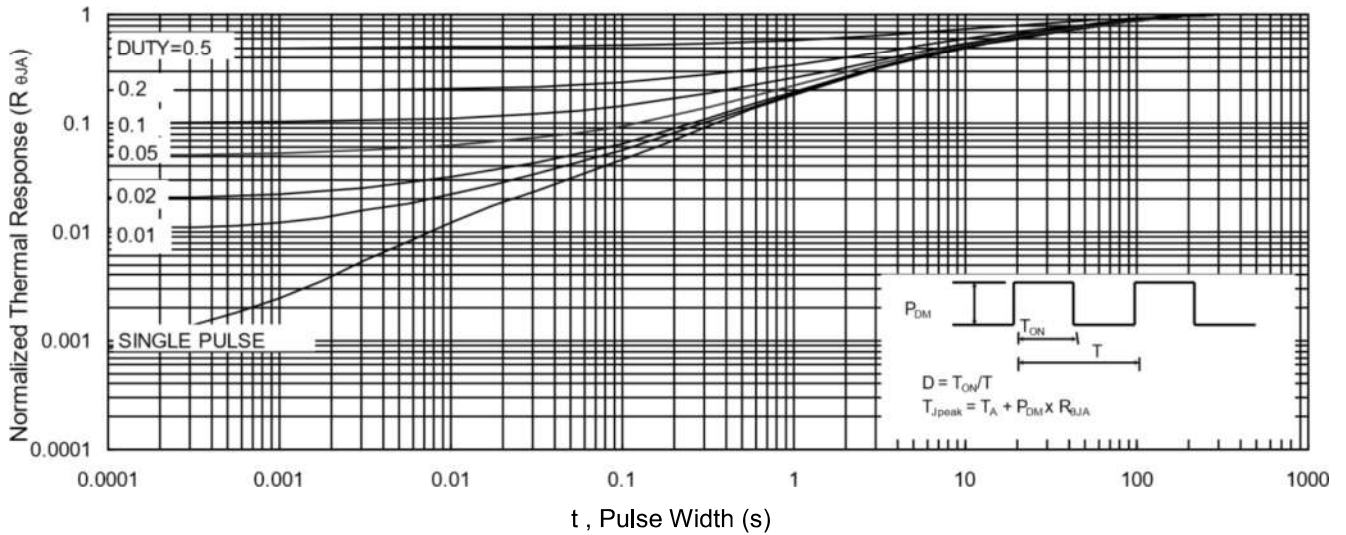


Fig.9 Normalized Maximum Transient Thermal Impedance

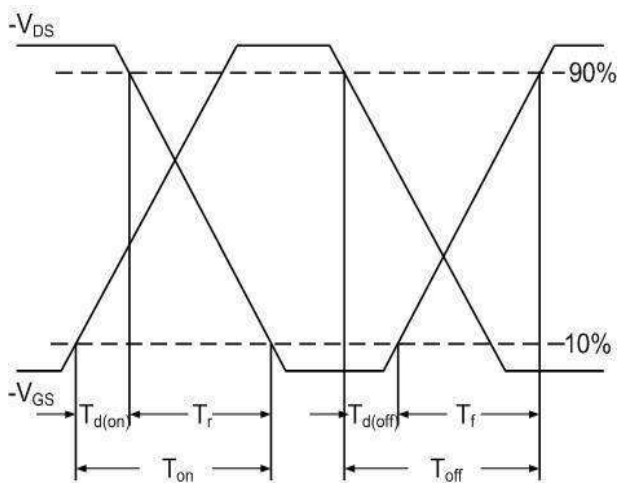


Fig.10 Switching Time Waveform

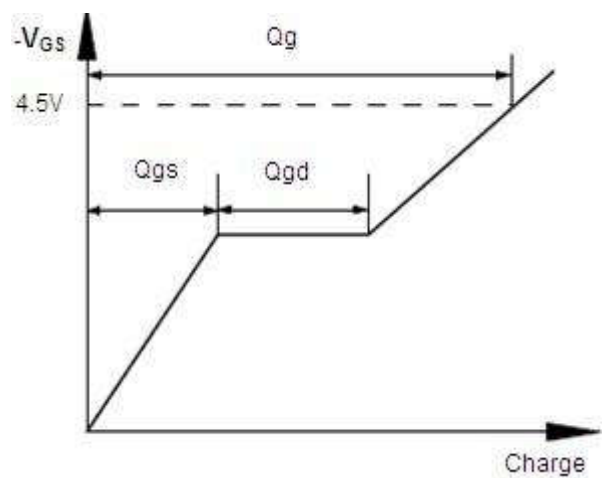


Fig.11 Gate Charge Waveform

Ordering information

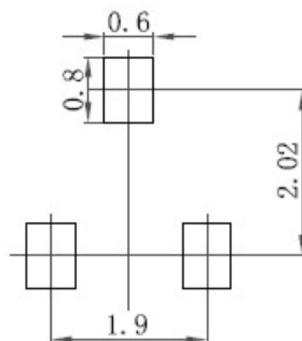
| Package | Packing Description | Base Quantity | Packing Quantity |
|---------|---------------------|---------------|-------------------------------|
| SOT-23 | Tape/Reel,7"reel | 3000pcs/Reel | 24000PCS/Box 120000PCS/Carton |

Package Dimensions

SOT-23

| Dim. | Millimeter (mm) | | mil | |
|------|-----------------|------|------|------|
| | Min. | Max. | Min. | Max. |
| A | 0.9 | 1.15 | 35 | 45 |
| A1 | 0.1 | | 3.9 | |
| bp | 0.38 | 0.48 | 15 | 19 |
| C | 0.09 | 0.15 | 3.54 | 5.9 |
| D | 2.8 | 3.0 | 110 | 118 |
| E | 1.2 | 1.4 | 47 | 55 |
| E | 1.9 | | 75 | |
| E1 | 0.95 | | 37 | |
| HE | 2.1 | 2.55 | 83 | 100 |
| Lp | 0.15 | 0.45 | 5.9 | 18 |
| Q | 0.45 | 0.55 | 18 | 22 |
| v | 0.2 | | 7.9 | |
| W | 0.1 | | 4 | |

The recommended mounting pad size



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